

U.S. Patent Application Serial No.: 09/899,267  
Amendment Under 37 C.F.R. §1.111 dated June 25, 2004  
Response to the Office Action of March 26, 2004

### **REMARKS**

Claims 1 – 15 remain pending in the present application. Claims 6-13 were merely objected to as a dependent upon a rejected base claim, but are otherwise allowable. The rejections set forth in the Office Action are respectfully traversed below.

### **Prior Art Rejections**

Claims 1, 3-5, and 14-15 were rejected under 35 USC § 102 over *Ueno et al.* (US 2002/0020780). However, it is submitted that the prior art does not teach or suggest all the features recited in the present claimed invention.

Amended independent claim 1 specifies the specific conductivity types as follows: “wherein said first source/drain region includes: a second conductivity type first impurity region formed on a first layer consisting of a first conductivity type semiconductor; and a first conductivity type second impurity region formed inside said first impurity region.” The cited prior art does not teach or suggest corresponding conductivity types for the various layers.

In particular, the Office Action alleged that reference no. 15 of *Ueno* corresponds to the present claimed “second conductivity type first impurity region.” The Office Action alleged that reference nos. 14/13 correspond to the present claimed “first conductivity type second impurity region.” The Office action also alleged that reference no. 1 corresponds to the present claimed first layer consisting of the first conductivity type semiconductor.

However, layers 1 and 15 of *Ueno* have the same conductivity types – not the different first and second conductivity types recited in claim 3. All the drawings of *Ueno*, as well as the

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descriptions of all 17 embodiments in **Ueno**, describe the substrate 1 as a "p-type substrate." In addition, all the descriptions of the "pocket region 15" indicate that it is a  $p^+$  conductivity type layer. Alternatives include the pocket region 15 being a  $p^{++}$  conductivity type. Basically, both layers 1 and 15 of **Ueno** have the *same* p-type conductivity type – not the present claimed first and second conductivity types.

In addition, if the p-type substrate 1 of **Ueno** constitutes a "first conductivity type" semiconductor, there is an apparent contradiction by asserting that n or  $n^+$  type regions 14/13 also constitutes the same "first conductivity type."

Therefore, **Ueno** does not teach or suggest the present claimed invention. If the Examiner believes that this application is not now in condition for allowance, the Examiner is requested to contact Applicant's undersigned attorney to arrange for an interview to expedite the disposition of this case.

If this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees that may be due with respect to this paper may be charged to Deposit Account No. 50-2866.

Respectfully submitted,

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